

Silicon NPN Power Transistors

2SD1279

DESCRIPTION

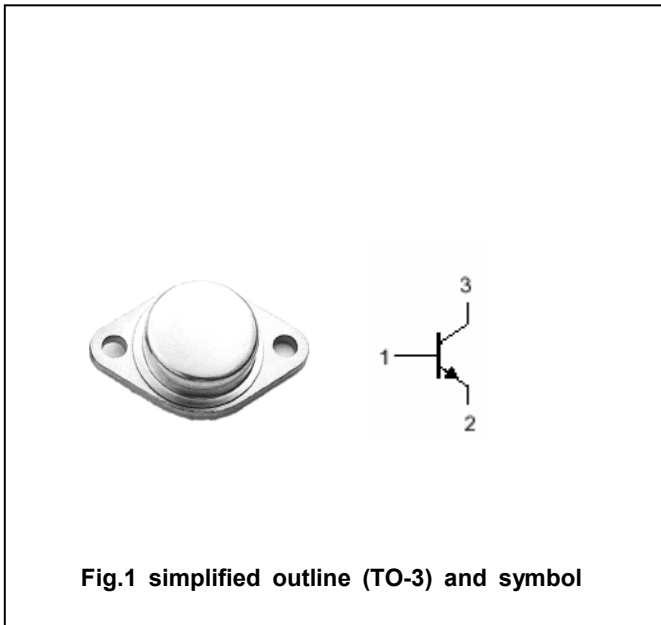
- With TO-3 package
- High voltage;high speed
- Low collector saturation voltage

APPLICATIONS

- Color TV horizontal deflection output applications
- Switching regulator applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1400	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A; I _B =2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =8A; I _B =2A			1.6	V
I _{CB0}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μA
I _{EB0}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	8	22		
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		3		MHz
C _{OB}	Collector output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		165		pF
t _f	Fall time	I _{CP} =7A ; I _{B1(end)} =1.5A			1.0	μs

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)